

IN THE CLAIMS

The following is a complete listing of the claims, which replaces all previous versions and listings of the claims.

1. (Currently Amended) A method for forming a die, the method comprising:

forming a die on a wafer, said die having one or more lateral edges, an active portion comprising integrated circuitry, and an inactive portion formed between said active portion and at least one lateral edge of said one or more lateral edges of said die, wherein said die has at least one input bond pad formed on said active portion;

forming at least one test pad on said die; and

forming a conductive path between said at least one input bond pad and said at least one test pad, wherein a portion of said conductive path is formed on said inactive portion of said die between said at least one lateral edge of said die and said active portion of said die, wherein an additional portion of said conductive path is formed on said wafer outside of said die.

2. (Original) The method of claim 1, said forming at least one test pad comprises forming at least one test pad on said active portion of said die.

3. (Currently Amended) The method of claim 2, said active portion being surrounded by said inactive portion, ~~wherein said conductive path extends from said at least one input bond pad to said inactive portion and from said inactive portion to said at least one test pad.~~

4. (Canceled)

5. (Original) The method of claim 1, further comprising severing said conductive path at a point outside of said active portion of said die.

6. (Original) The method of claim 3, further comprising severing said conductive path at a point within said inactive portion.

7. (Currently Amended) The method of claim [[4]] 1, further comprising severing said conductive path at a point outside said die.

8. (Original) The method of claim 1, wherein said at least one test pad is of a sufficient size so as to be accessible by a testing apparatus.

9. (Currently Amended) A die assembly formed on a wafer, the die assembly comprising:

a die formed on the wafer, said die having one or more lateral edges, an active portion comprising integrated circuitry, and an inactive portion formed between said active portion and at least one lateral edge of said one or more lateral edges of said die;

at least one input bond pad formed on said active portion of said die;

at least one test pad formed entirely on said die, wherein said at least one test pad is formed on said active portion of said die; and

a conductive path that electrically couples said at least one input bond pad to said at least one test pad, wherein a portion of said conductive path is formed on said inactive portion between said at least one lateral edge of said die and said active portion of said die, said active portion of said die being surrounded by said inactive portion of said die, wherein said conductive path extends from said at least one input bond pad to said inactive portion and from said inactive portion to said at least one test pad.

10. (Canceled)

11. (Canceled)

12. (Currently Amended) The die assembly of claim 9, said die being surrounded by a non-conducting scribe area of the wafer, ~~wherein an additional portion of said conductive path is formed on said non-conducting scribe area.~~

13. (Original) The die assembly of claim 9, wherein said at least one test pad is of sufficient size so as to be accessible by a testing apparatus.

14. (Currently Amended) A method for preparing a die on a wafer for testing by a testing apparatus, the method comprising:

forming a die on a wafer, said die having one or more lateral edges, an active portion comprising integrated circuitry, and an inactive portion formed between said active portion and at least one lateral edge of said one or more lateral edges of said die;

forming a plurality of input bond pads on said active portion;

forming a plurality of test pads entirely on said die, said plurality of test pads accessible to the testing apparatus, at least one of said plurality of test pads corresponding to at least one of said plurality of input bond pads;

forming a conductive path between said at least one of said plurality of test pads and said at least one of said plurality of input bond pads, wherein a portion of said conductive path is formed on said inactive portion between said at least one lateral edge of said die and said active portion of said die, said active portion being surrounded by said inactive portion, wherein said conductive path extends from said at least one input bond pad to said inactive portion and from said inactive portion to said at least one test pad; and

testing said die by contacting said at least one of said plurality of test pads with the testing apparatus.

15. (Previously Presented) The method of claim 14, wherein said plurality of test pads are formed on said active portion of said die.

16. (Canceled)

17. (Canceled)

18. (Original) The method of claim 14, further comprising severing said conductive path at a point outside of said active portion of said die.

19. (Currently Amended) The method of claim [[16]] 14, further comprising severing said conductive path at a point within said inactive portion.

20. (Canceled)

21. (Original) The method of claim 14, wherein said at least one of said plurality of test pads is larger in size than said at least one of the plurality of input bond pads.

22. (Currently Amended) A die comprising:
one or more lateral edges;
an active portion comprising integrated circuitry;
an inactive portion formed between said active portion and at least one lateral edge of said one or more lateral edges of said die;
a plurality of input bond pads formed on said active portion;
a plurality of test pads formed entirely on said die; and

a plurality of conductive lines, wherein each of said conductive lines is initially formed to electrically couple at least one of said plurality of input bond pads to at least one of said plurality of test pads, and wherein a portion of said each of said conductive lines is formed on said inactive portion between said at least one lateral edge of said die and said active portion of the die, wherein an additional portion of said each of said conductive lines is formed outside of the die.

23. (Original) The die of claim 22, said plurality of test pads formed on said active portion of said die.

24. (Currently Amended) The die of claim 22, said active portion being surrounded by said inactive portion, ~~wherein said each of said conductive lines extends from said at least one input bond pad to said inactive portion and from said inactive portion to said at least one test pad.~~

25. (Canceled)

26. (Currently Amended) The die of claim [[25]] 22, the die being formed on a wafer, wherein said portion of said each of said conductive lines is configured to be severed when the die is separated from said wafer.

27. (Original) The method of claim 22, wherein said at least one of said plurality of test pads is larger in size than said at least one of said plurality of input bond pads.

28. (Previously Presented) A die comprising:
an active portion comprising integrated circuitry;
a plurality of input bond pads formed on said active portion;
a plurality of test pads formed on said die;

a plurality of conductive lines, wherein each of said conductive lines is initially formed to electrically couple at least one of said plurality of input bond pads to at least one of said plurality of test pads, and wherein a portion of said each of said conductive lines is formed on a scribe area outside the die.